

## N-Channel Enhancement Mode Field Effect Transistor

### Product Summary

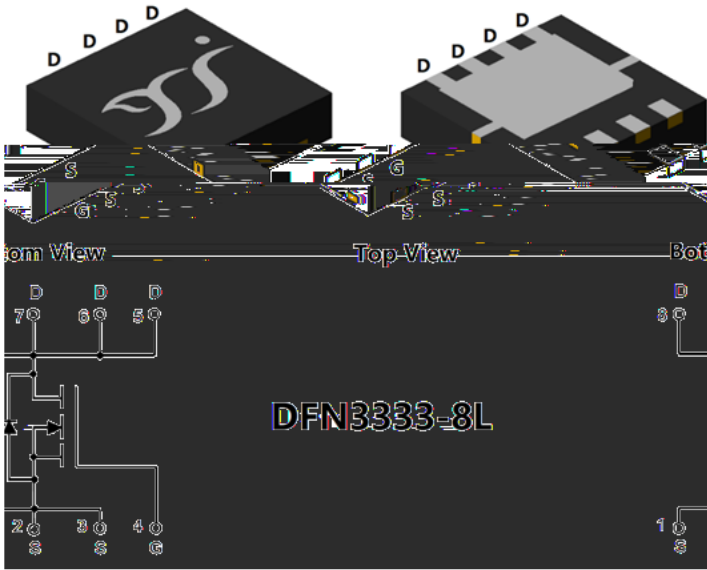
$V_{DS}$	40 V
$I_D$	20 A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	14.0 mohm
$R_{DS(ON)}$ (at $V_{GS}=4.5V$ )	18.5 mohm
100% EAS Tested	
100% $V_{DS}$ Tested	
ESD Level (HBM)	Class 1B

### General Description

Excellent package for heat dissipation  
 High density cell design for low  $R_{DS(ON)}$   
 meets UL 94 V-0 Flammability Rating  
 Halogen Free

### Applications

High current load applications  
 Load switching  
 Hard switched and high frequency circuits  
 Uninterruptible power supply



### Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	40	V
Gate-source Voltage		$V_{GS}$	20	V
Drain Current	$T_C=25$	$I_D$	20	A
	$T_C=100$		14	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	90	A
Single Pulse Avalanche Energy <sup>B</sup>		$E_{AS}$	70	mJ
Total Power Dissipation	$T_C=25$	$P_D$	21	W
	$T_A=25$		2.34	
Thermal Resistance Junction-to-Case		$R_{JC}$	5.9	/W
		$R_{JA}$	53.4	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 +150	

### Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJQ20N04A	F1	Q20N04	5000	10000	100000	13 reel

**YJQ20**



## Typical Performance Characteristics

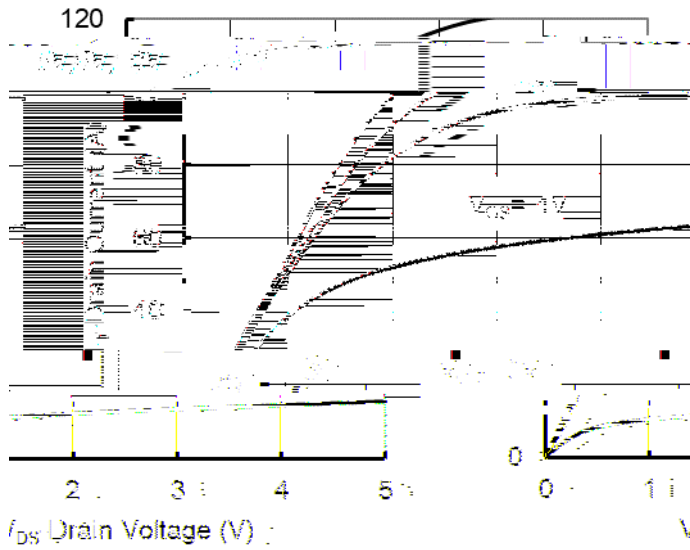


Figure 1. Output Characteristics

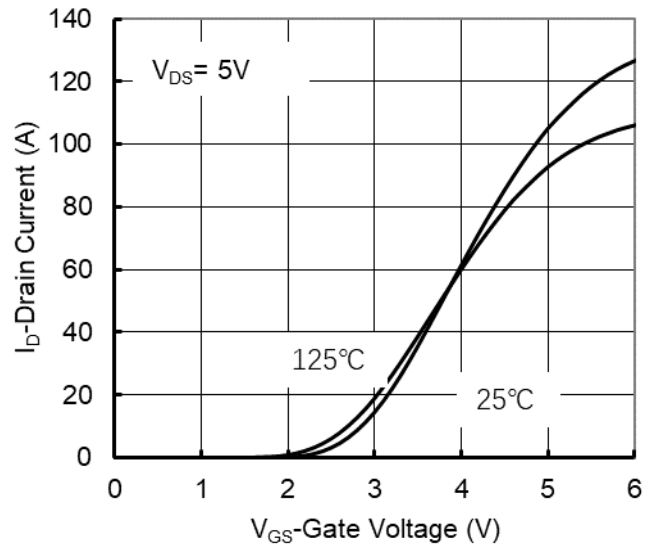


Figure 2. Transfer Characteristics

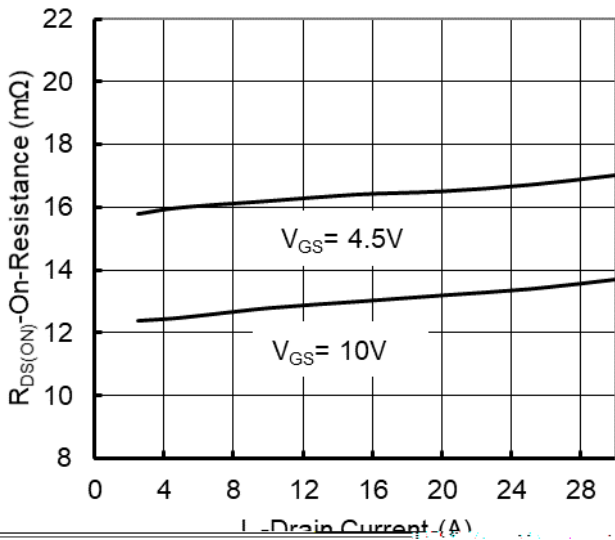


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

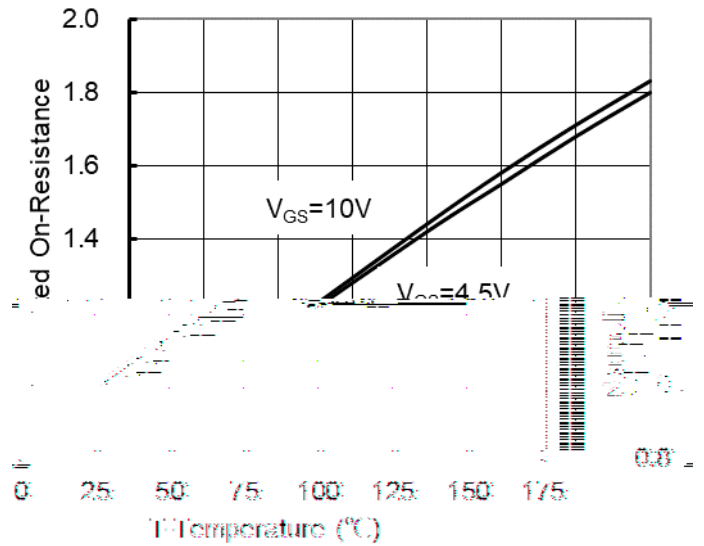


Figure 4. On-Resistance vs. Junction Temperature

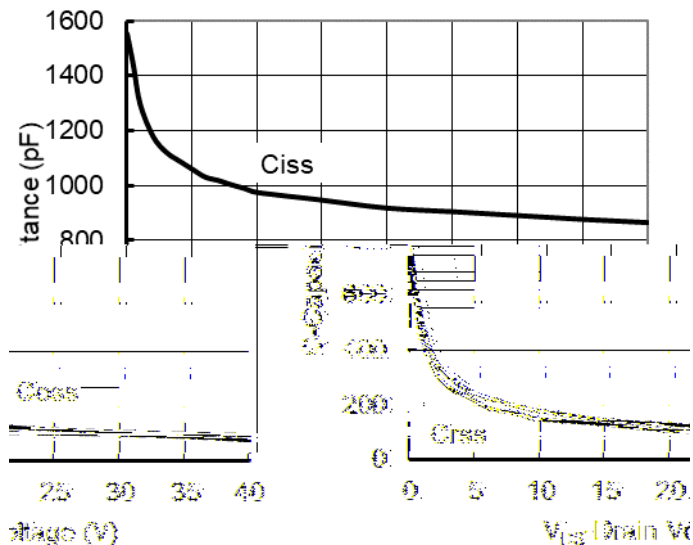


Figure 5. Capacitance Characteristics

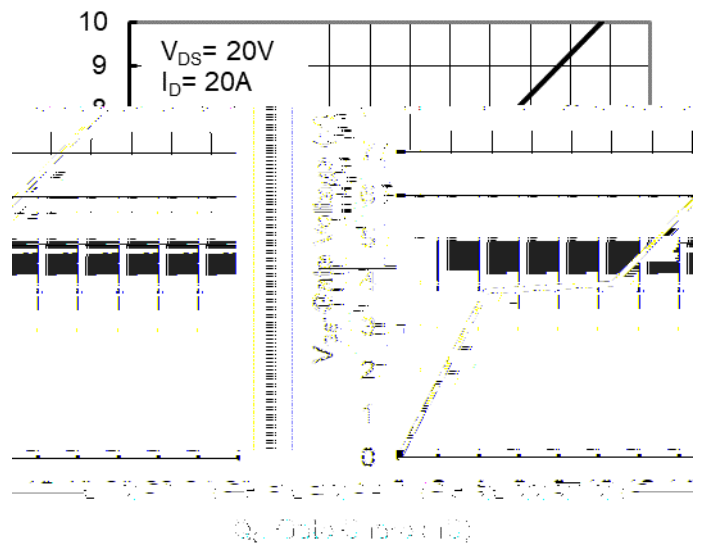
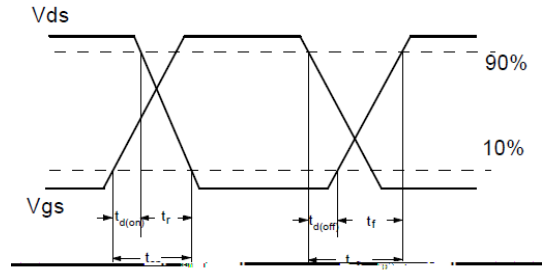
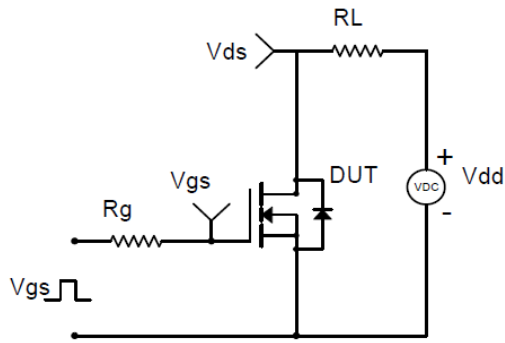
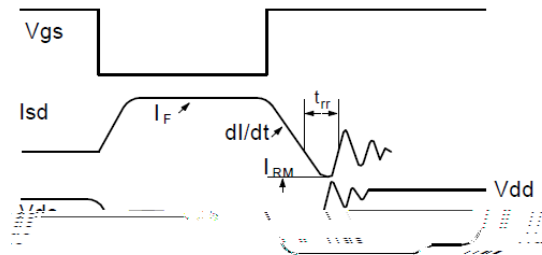
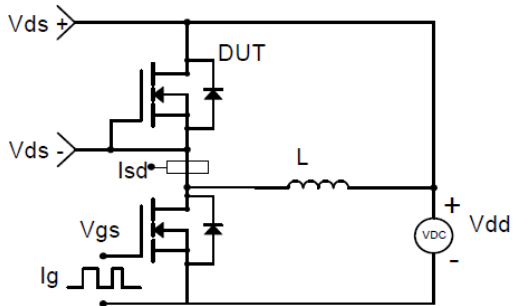


Figure 6. Gate Charge

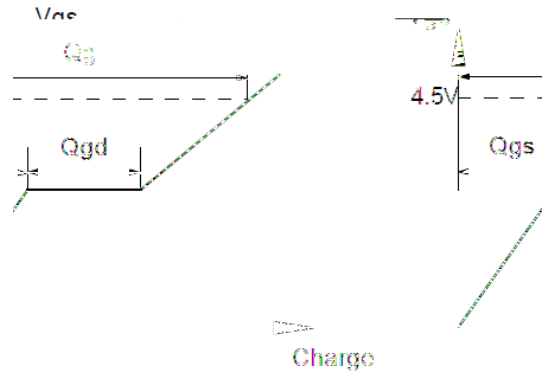
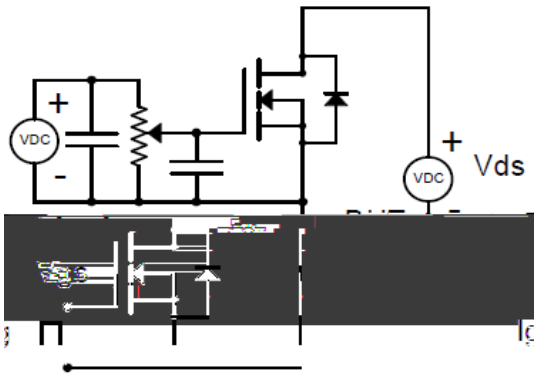




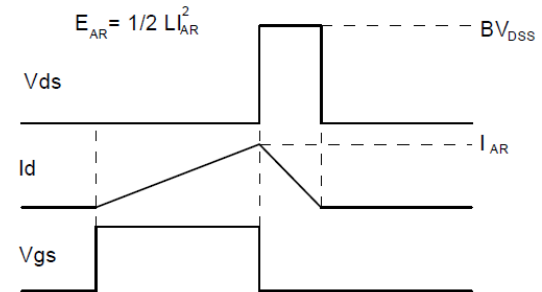
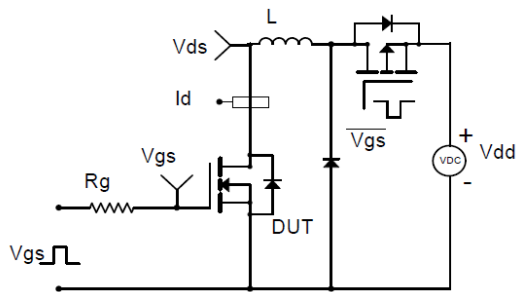
**Resistive Switching Test Circuit & Waveforms**



**Diode Recovery Test Circuit & Waveforms**



**Gate Charge Test Circuit & Waveform**

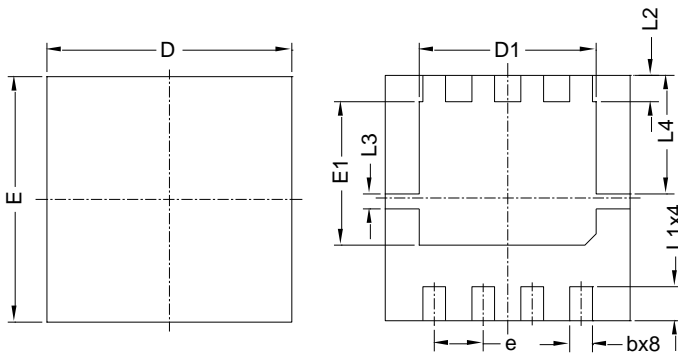


**Unclamped Inductive Switching (UIS) Test Circuit & Waveforms**



# YJQ20N04A

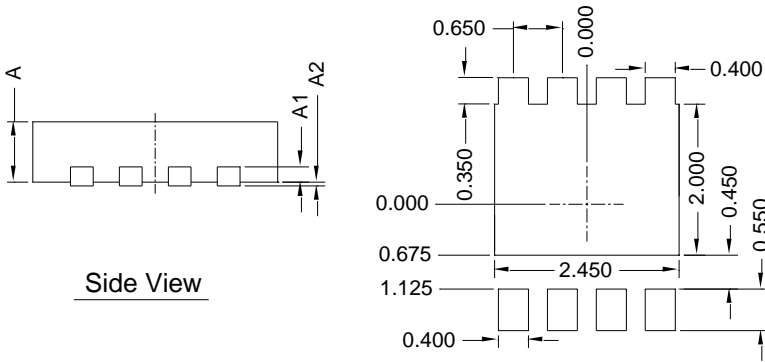
## DFN3333-8L-A-0.8MM Package information



Top View

Bottom View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	3.15	3.25	3.35
E	3.15	3.25	3.35
A	0.70	0.80	0.90
A1	0.20 BSC		
A2			0.10
D1	2.20	2.35	2.50
E1	1.80	1.90	2.00
L1	0.35	0.45	0.55
L2	0.35 BSC		
L3	0.20 BSC		
L4	1.57 BSC		
b	0.20	0.30	0.40
e	0.65 BSC		



Side View

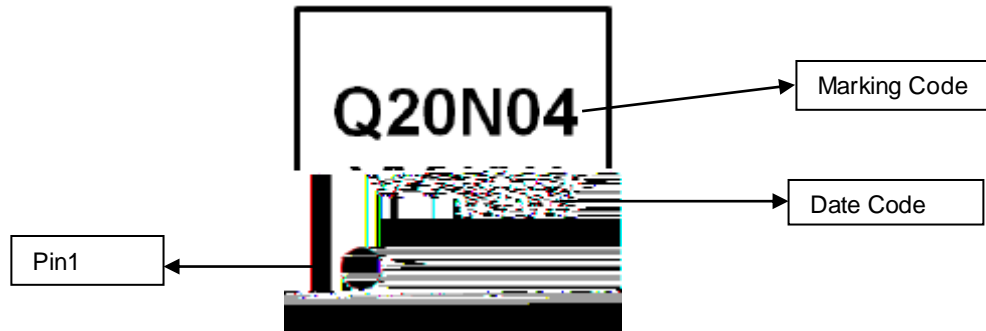
Suggested Solder Pad Layout  
Top View

Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.10\text{mm}$ .
3. The pad layout is for reference purposes only.



Marking Information



Note

1. All marking is at middle of the product body
2. All marking is in laser printing
3. Q20N04 is marking code, YYWW is date code,
4. Body color: Black

